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## PATENT ABSTRACTS OF JAPAN

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(71) Applicant: FUJITSU LTD

(72) Inventor: AOYAMA ATSUYUKI

(74) Representative:

## (54) MANUFACTURE OF SEMICONDUCTOR DEVICE

## (57) Abstract:

PURPOSE: To perform etching of an Si oxide film and an Si nitride film by a dry method without damaging a substrate by etching the Si oxide film and the Si nitride film by exposing these to F-group gas containing specific atoms, and mixed gas of aforesaid F-group gas and H2O, H2.

CONSTITUTION: Etching of an Si oxide film 3 and an Si nitride film 4 is performed by exposing these to F-group gas containing F-atoms of HF, F2, XeF2 and to mixed gas of aforesaid F-group gas and H2O, H2. Etching of a nitride film, an oxide film is performed according to an etching property, thickness of semiconductor constitution materials such as single Si, polySi, a nitride film, an oxide film and the kinds of F-group gas, and the materials around them are made to remain. During an etching process, ultraviolet light is directly applied to F-group gas or a substrate 1. After the etching process, annealing is performed. After etching or annealing processes, again a film 6 is formed. Directly before finishing the etching process, F-group gas is changed to F-group gas having low etching speed of the semiconductor substrate.

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